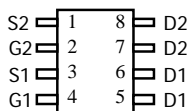




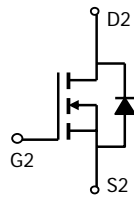
AO4619

Complementary Enhancement Mode Field Effect Transistor

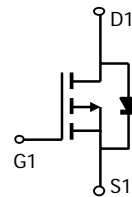
<p>General Description</p> <p>The AO4619 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in inverter and other applications. <i>Standard Product AO4619 is Pb-free (meets ROHS & Sony 259 specifications).</i></p>	<p>Features</p> <table border="0"> <tr> <td>n-channel</td> <td>p-channel</td> </tr> <tr> <td>$V_{DS} (V) = 30V$</td> <td>-30V</td> </tr> <tr> <td>$I_D = 7.4A (V_{GS}=10V)$</td> <td>-5.2A ($V_{GS} = -10V$)</td> </tr> <tr> <td>$R_{DS(ON)}$</td> <td>$R_{DS(ON)}$</td> </tr> <tr> <td>< 24mΩ ($V_{GS}=10V$)</td> <td>< 48mΩ ($V_{GS} = -10V$)</td> </tr> <tr> <td>< 36mΩ ($V_{GS}=4.5V$)</td> <td>< 74mΩ ($V_{GS} = -4.5V$)</td> </tr> </table>	n-channel	p-channel	$V_{DS} (V) = 30V$	-30V	$I_D = 7.4A (V_{GS}=10V)$	-5.2A ($V_{GS} = -10V$)	$R_{DS(ON)}$	$R_{DS(ON)}$	< 24m Ω ($V_{GS}=10V$)	< 48m Ω ($V_{GS} = -10V$)	< 36m Ω ($V_{GS}=4.5V$)	< 74m Ω ($V_{GS} = -4.5V$)
n-channel	p-channel												
$V_{DS} (V) = 30V$	-30V												
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< 36m Ω ($V_{GS}=4.5V$)	< 74m Ω ($V_{GS} = -4.5V$)												



SOIC-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^F	I_D	$T_A=25^\circ C$	7.4	-5.2
		$T_A=70^\circ C$	6	-4.2
Pulsed Drain Current ^B	I_{DM}	35	-25	A
Power Dissipation ^A	P_D	$T_A=25^\circ C$	2	2
		$T_A=70^\circ C$	1.3	1.3
Avalanche Current ^B	I_{AR}	13	11	A
Repetitive avalanche energy 0.3mH ^B	E_{AR}	25	18	mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	50	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		n-ch	82	110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	n-ch	41	50	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	50	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		p-ch	82	110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	p-ch	41	50	$^\circ C/W$

N-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1	1.62	3	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	35			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =7.4A T _J =125°C		19 27	24 34	mΩ
		V _{GS} =4.5V, I _D =6A		29	36	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =7.4A		24		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		621	820	pF
C _{oss}	Output Capacitance			118		pF
C _{riss}	Reverse Transfer Capacitance			85		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.8	1.5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =7.4A		11.3		nC
Q _g (4.5V)	Total Gate Charge			5.7		nC
Q _{gs}	Gate Source Charge			2.1		nC
Q _{gd}	Gate Drain Charge			3		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =2Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			3.1		ns
t _{D(off)}	Turn-Off Delay Time			15.1		ns
t _f	Turn-Off Fall Time			2.7		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =7.4A, dI/dt=100A/μs		15.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =7.4A, dI/dt=100A/μs		7.1		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t_s ≤ 10s thermal resistance rating.

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N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

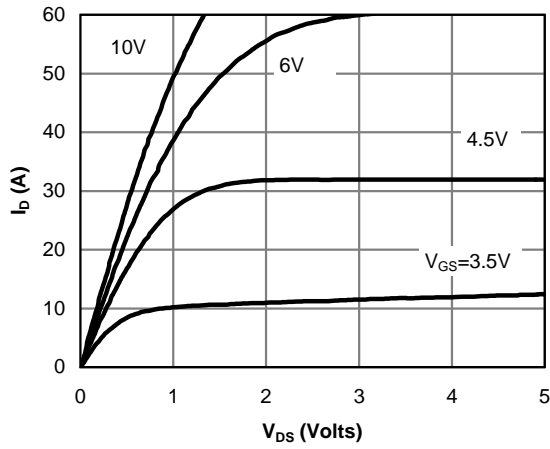


Figure 1: On-Region Characteristics

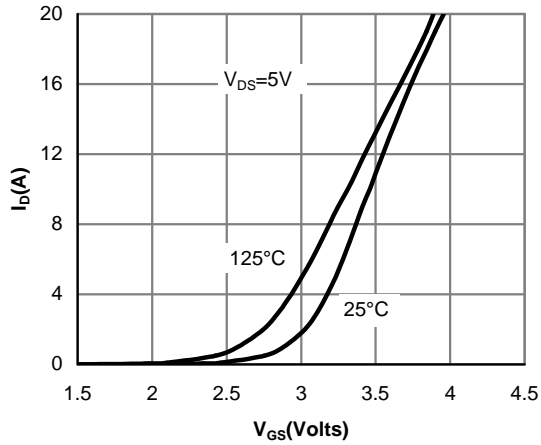


Figure 2: Transfer Characteristics

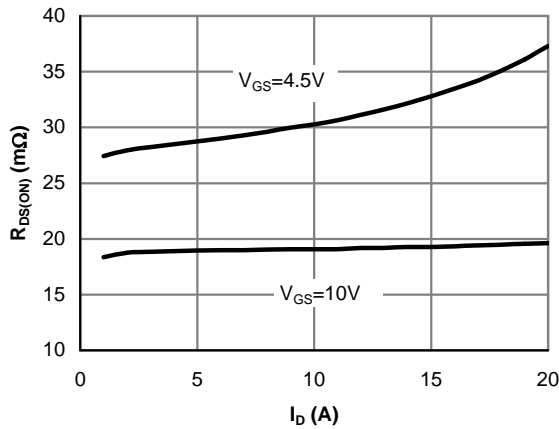


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

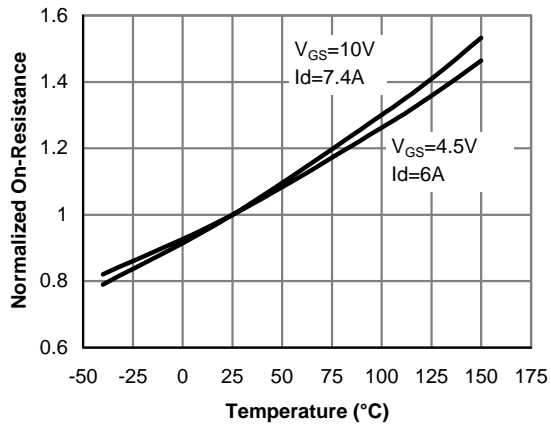


Figure 4: On-Resistance vs. Junction Temperature

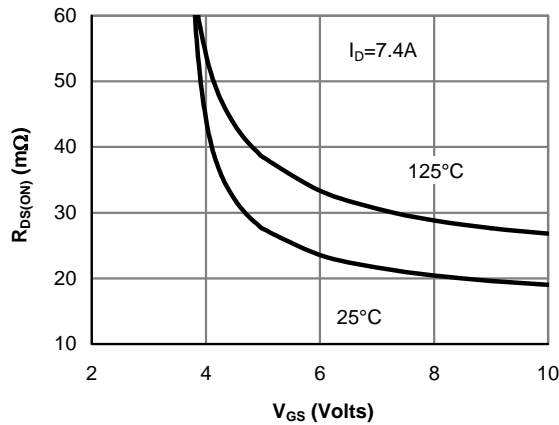


Figure 5: On-Resistance vs. Gate-Source Voltage

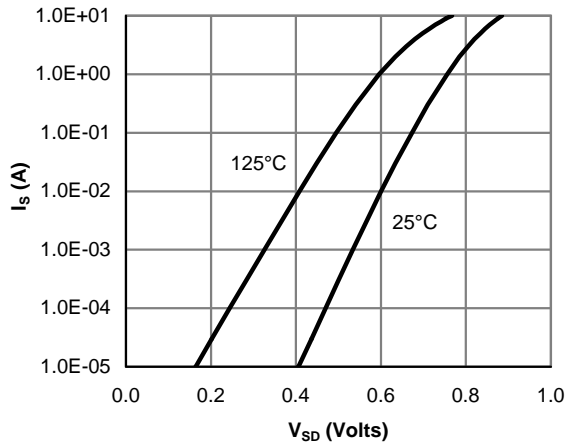


Figure 6: Body-Diode Characteristics

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

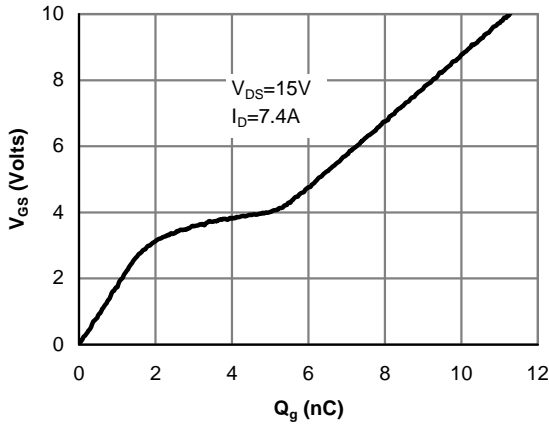


Figure 7: Gate-Charge Characteristics

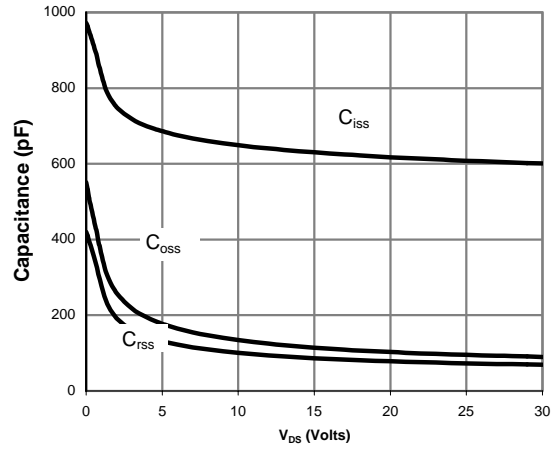


Figure 8: Capacitance Characteristics

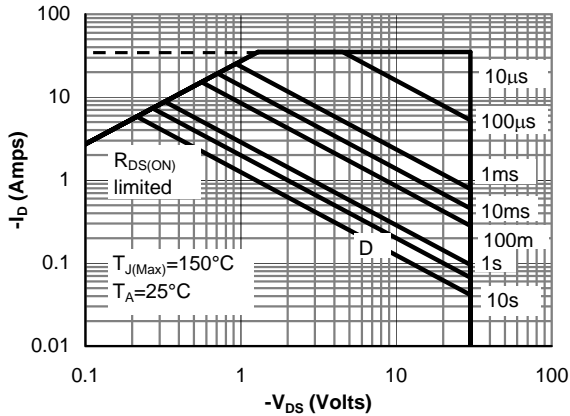


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

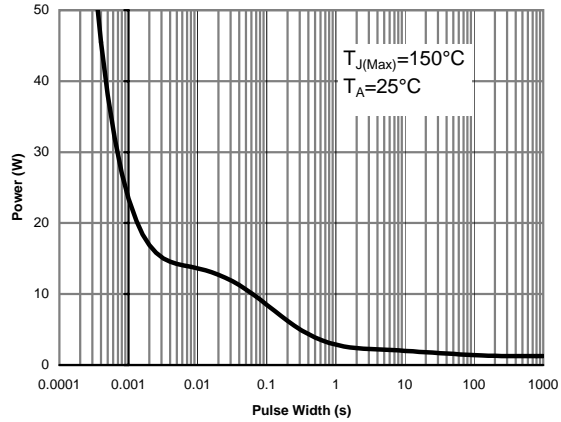


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

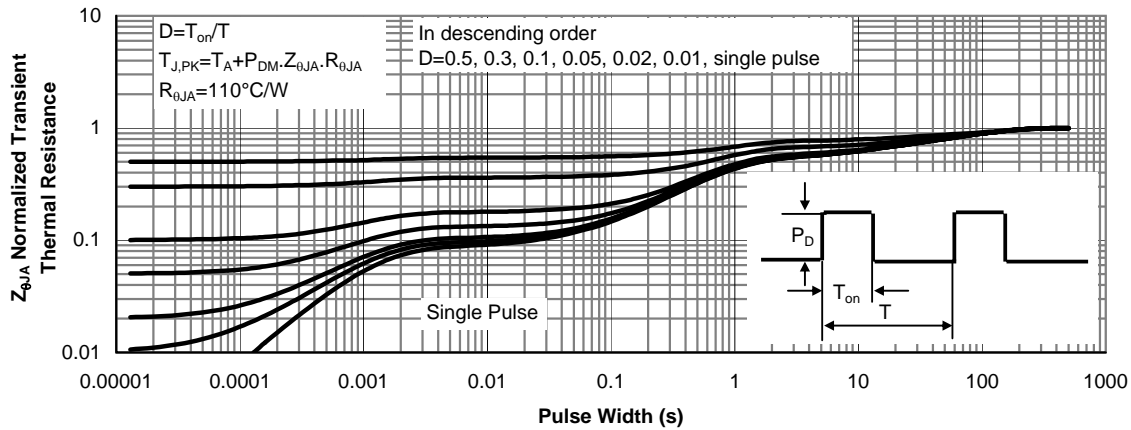


Figure 11: Normalized Maximum Transient Thermal Impedance

P-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1	-1.88	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-5.2\text{A}$ $T_J=125^\circ\text{C}$		38 55	48 69	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-4\text{A}$		59	74	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-5.2\text{A}$		11		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.77	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.5	A
DYNAMIC PARAMETERS						
C_{ISS}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		680	816	pF
C_{OSS}	Output Capacitance			115		pF
C_{RSS}	Reverse Transfer Capacitance			86		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		8	12	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-5.2\text{A}$		12.7		nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			6.4		nC
Q_{gs}	Gate Source Charge			2		nC
Q_{gd}	Gate Drain Charge			4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=3\Omega$, $R_{GEN}=3\Omega$		7.7		ns
t_r	Turn-On Rise Time			6.8		ns
$t_{D(off)}$	Turn-Off DelayTime			20		ns
t_f	Turn-Off Fall Time			10		ns
t_{rr}	Body Diode Reverse Recovery Time		$I_F=-5.2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		22	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5.2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		15		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

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P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

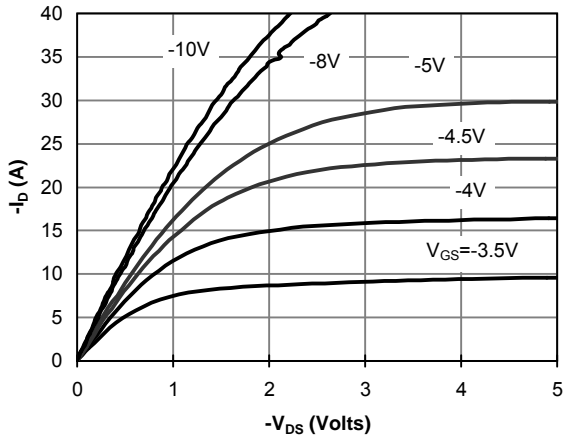


Figure 1: On-Region Characteristics

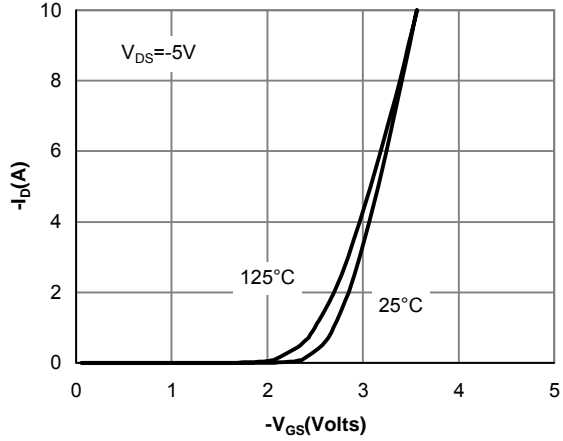


Figure 2: Transfer Characteristics

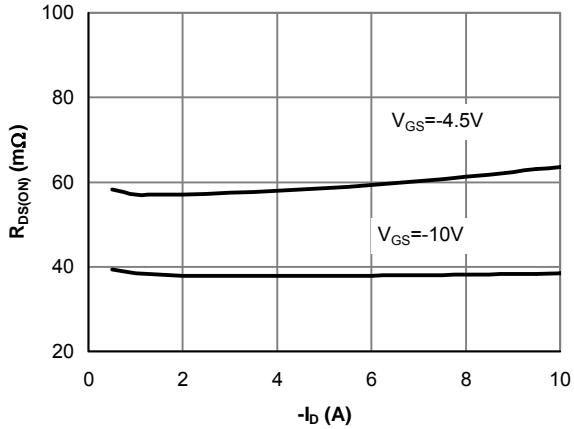


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

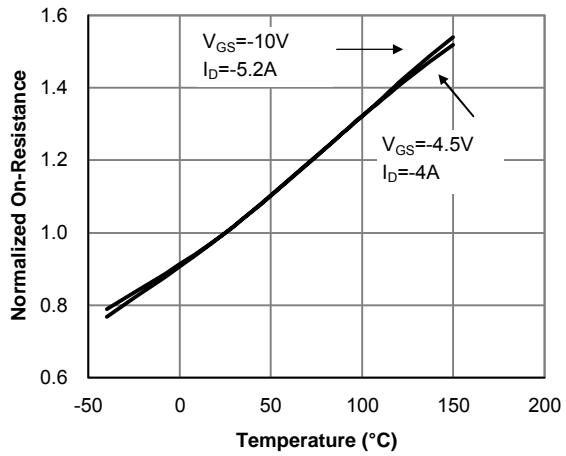


Figure 4: On-Resistance vs. Junction Temperature

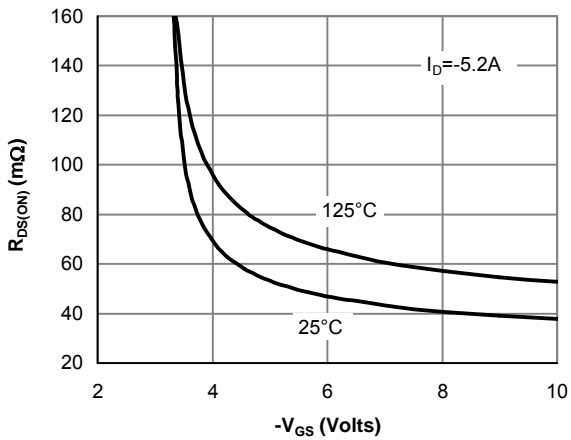


Figure 5: On-Resistance vs. Gate-Source Voltage

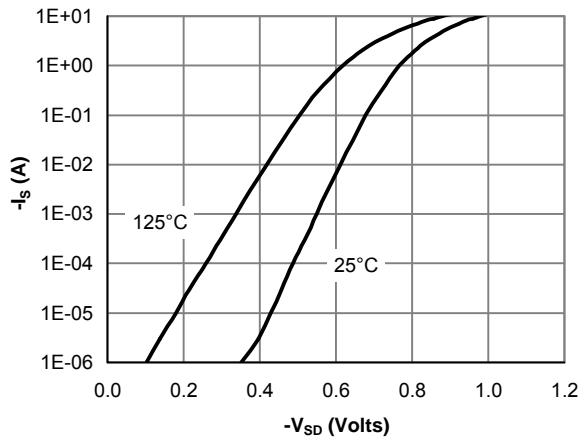


Figure 6: Body-Diode Characteristics

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

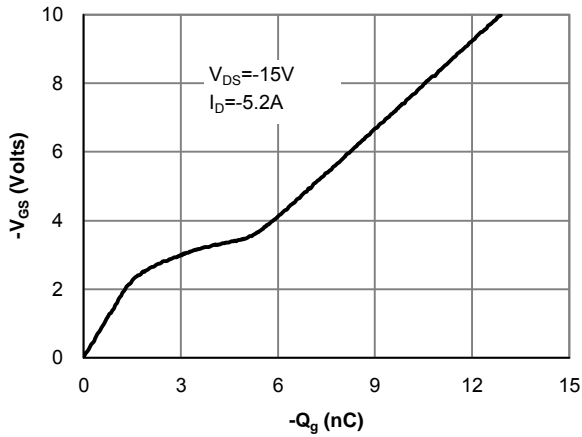


Figure 7: Gate-Charge Characteristics

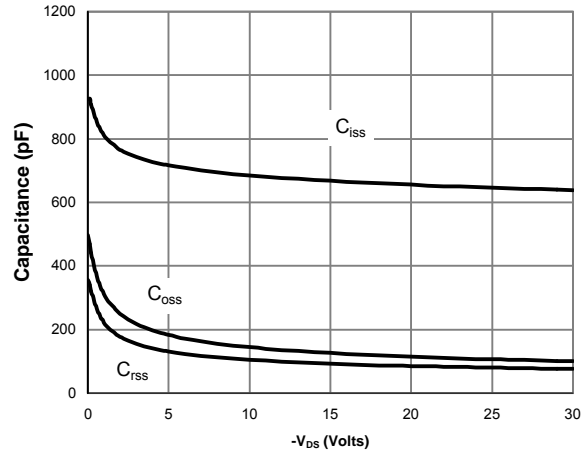


Figure 8: Capacitance Characteristics

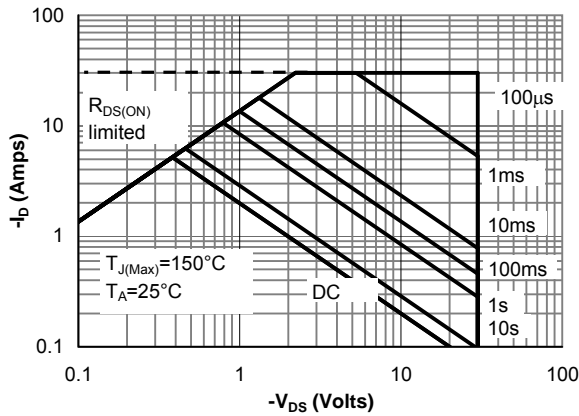


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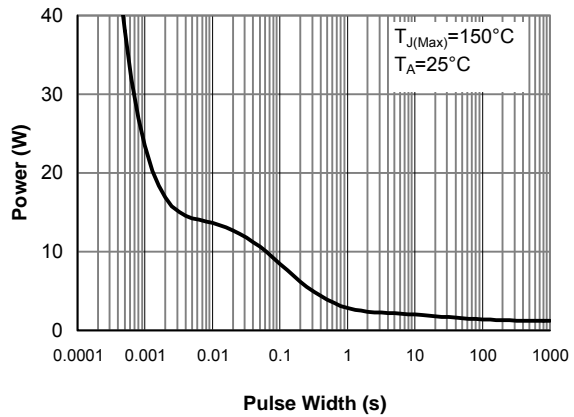


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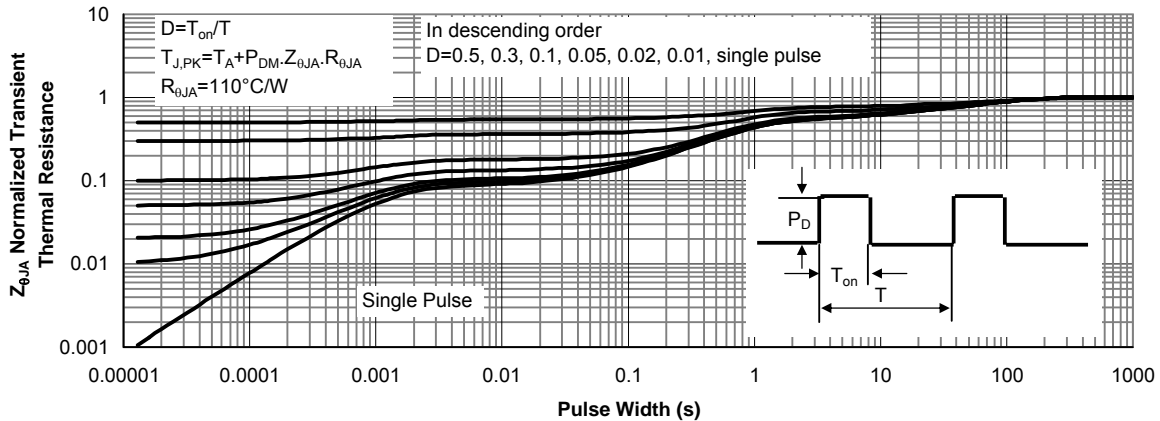


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